

FEATURES

128-position

End-to-end resistance 5 k Ω , 10 k Ω , 50 k Ω , 100 k Ω Ultra-Compact SC70-6 (2 mm × 2.1 mm) package I²C compatible interface Full read/write of wiper register Power-on preset to midscale Single supply 2.7 V to 5.5 V Low temperature coefficient 35 ppm/°C Low power, I_{DD} = 3 μ A Typical Wide operating temperature -40°C to +125°C Evaluation board available

APPLICATIONS

Mechanical potentiometer replacement in new designs Transducer adjustment of pressure, temperature, position, chemical, and optical sensors RF amplifier biasing Automotive electronics adjustment Gain control and offset adjustment

GENERAL OVERVIEW

The AD5246 provides a compact 2x2.1mm packaged solution for 128 position adjustment applications. This device performs the same electronic adjustment function as a variable resistor. Available in four different end-to-end resistance values (5k, 10k, 50k, 100k) these low temperature coefficient devices are ideal for high accuracy and stability variable resistance adjustments.

The wiper settings are controllable through the I²C compatible digital interface, which can also be used to read back the present wiper register control word. The resistance between the wiper and either end point of the fixed resistor varies linearly with respect to the digital code transferred into the RDAC latch.

Operating from a 2.7 to 5.5 volt power supply and consuming less than $3\mu A$ allows for usage in portable battery operated applications.

128-Position I²C Compatible Digital Resistor

AD5246

FUNCTIONAL BLOCK DIAGRAM



Figure 1.

PIN CONFIGURATION

1	V _{DD}	В	6
2	GND	W	5
3	SCL	SDA	4

Figure 2.

Note:

The terms digital potentiometer, VR, and RDAC are used interchangeably.

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 One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.

 Tel: 781.329.4700
 www.analog.com

 Fax: 781.326.8703
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AD5246

Preliminary Technical Data

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ELECTRICAL CHARACTERISTICS—5 k Ω VERSION

(V_{DD} = 5 V \pm 10%, or 3 V \pm 10%; V_A = +V_{DD}; -40°C < T_A < +125°C; unless otherwise noted.)

Table 1.

Parameter	Symbol	Conditions	Min	Typ ¹	Max	Unit
DC CHARACTERISTICS—RHEOSTAT MODE						
Resolution	Ν				7	Bits
Resistor Differential Nonlinearity ²	R-DNL	R _{WB} ,	-1.5	±0.1	+1.5	LSB
Resistor Integral Nonlinearity ²	R-INL	R _{WB} ,	-4	±0.75	+4	LSB
Nominal Resistor Tolerance ³	ΔR_{AB}	$T_A = 25^{\circ}C$	-30		+30	%
Resistance Temperature Coefficient	$\Delta R_{AB} / \Delta T$	Wiper = no connect		45		ppm/°C
Wiper Resistance	Rw			50	120	Ω
RESISTOR TERMINALS						
Voltage Range⁴	V _{B,W}		GND		V _{DD}	V
Capacitance ⁵ B	Св	f = 1 MHz, measured to GND, Code = 0x40		45		pF
Capacitance ⁵ W	Cw	f = 1 MHz, measured to GND, Code = 0x40		60		pF
Common-Mode Leakage	Ісм	$V_A = V_{DD}/2$		1		nA
DIGITAL INPUTS AND OUTPUTS						
Input Logic High	VIH		2.4			V
Input Logic Low	VIL				0.8	V
Input Logic High	VIH	$V_{DD} = 3 V$	2.1			V
Input Logic Low	VIL	$V_{DD} = 3 V$			0.6	V
Input Current	lı∟	$V_{IN} = 0 V \text{ or } 5 V$			±1	μΑ
Input Capacitance ⁵	CIL			5		рF
POWER SUPPLIES						
Power Supply Range	VDD RANGE		2.7		5.5	V
Supply Current	I _{DD}	$V_{IH} = 5 V \text{ or } V_{IL} = 0 V$		3	8	μA
Power Dissipation ⁶	P _{DISS}	$V_{IH} = 5 V \text{ or } V_{IL} = 0 V, V_{DD} = 5 V$			40	μW
Power Supply Sensitivity	PSS	$\Delta V_{DD} = +5 V \pm 10\%$, Code = Midscale		±0.02	±0.05	%/%
DYNAMIC CHARACTERISTICS ^{5, 7}						
Bandwidth –3dB	BW_5K	$R_{AB} = 5 k\Omega$, Code = 0x40		1.2		MHz
Total Harmonic Distortion	THDw	$V_{A} = 1 V rms, V_{B} = 0 V, f = 1 kHz$		0.05		%
Resistor Noise Voltage Density	en wb	$R_{WB} = 2.5 \text{ k}\Omega, \text{RS} = 0$		6		nV/√Hz

ELECTRICAL CHARACTERISTICS—10 k Ω , 50 k Ω , 100 k Ω VERSIONS

(V_{DD} = 5 V \pm 10%, or 3 V \pm 10%; V_A = +V_{DD}; -40°C < T_A < +125°C; unless otherwise noted.)

Table 2.

Parameter	Symbol	Conditions	Min	Typ ¹	Max	Unit
DC CHARACTERISTICS—RHEOSTAT MODE				1		
Resistor Differential Nonlinearity ²	R-DNL	R_{WB} , V_A = no connect	-1	±0.1	+1	LSB
Resistor Integral Nonlinearity ²	R-INL	R_{WB} , V_A = no connect	-2	±0.25	+2	LSB
Nominal Resistor Tolerance ³	ΔR_{AB}	$T_A = 25^{\circ}C$	-30		+30	%
Resistance Temperature Coefficient	$\Delta R_{AB} / \Delta T$	Wiper = no connect		45		ppm/°C
Wiper Resistance	Rw	$V_{DD} = 5 V$		50	120	Ω
RESISTOR TERMINALS						
Voltage Range⁴	V _{B,W}		GND		V _{DD}	V
Capacitance ⁵ B	CB	f = 1 MHz, measured to GND, Code = 0x40		45		pF
Capacitance ⁵ W	Cw	f = 1 MHz, measured to GND, Code = 0x40		60		pF
Common-Mode Leakage	I _{CM}	$V_A = V_{DD}/2$		1		nA
DIGITAL INPUTS AND OUTPUTS						
Input Logic High	VIH		2.4			V
Input Logic Low	VIL				0.8	V
Input Logic High	VIH	$V_{DD} = 3 V$	2.1			V
Input Logic Low	VIL	$V_{DD} = 3 V$			0.6	V
Input Current	lı∟	$V_{IN} = 0 V \text{ or } 5 V$			±1	μA
Input Capacitance⁵	CIL			5		рF
POWER SUPPLIES						
Power Supply Range	V _{DD RANGE}		2.7		5.5	V
Supply Current	IDD	$V_{IH} = 5 \text{ V or } V_{IL} = 0 \text{ V}$		3	8	μA
Power Dissipation ⁶	P _{DISS}				40	μW
Power Supply Sensitivity	PSS	$\Delta V_{DD} = +5 V \pm 10\%$, Code = Midscale		±0.02	±0.05	%/%
DYNAMIC CHARACTERISTICS ^{5, 7}				1		
Bandwidth –3dB	BW	$\label{eq:RAB} \begin{split} R_{AB} &= 10 \; k\Omega/50 \; k\Omega/100 \; k\Omega, \\ Code &= 0x40 \end{split}$		600/100/40		kHz
Total Harmonic Distortion	THDw	$V_A = 1 V \text{ rms}, f = 1 \text{ kHz}, R_{AB} = 10 \text{ k}\Omega$		0.05		%
Resistor Noise Voltage Density	en wb	$R_{WB} = 5 k\Omega, RS = 0$		9		nV/√Hz

TIMING CHARACTERISTICS—5 k Ω , 10 k Ω , 50 k Ω , 100 k Ω VERSIONS

 $(V_{DD} = +5V \pm 10\%, \text{ or } +3V \pm 10\%; V_A = V_{DD}; -40^{\circ}\text{C} < T_A < +125^{\circ}\text{C}; \text{ unless otherwise noted.})$

Table 3.

Parameter	Symbol	Conditions	Min	Typ ¹	Мах	Unit
I ² C INTERFACE TIMING CHARACTERISTICS ^{5, 8} (Specific	ations Apply	to All Parts)				
SCL Clock Frequency	f _{SCL}				400	kHz
t_{BUF} Bus Free Time between STOP and START	t1		1.3			μs
t _{HD;STA} Hold Time (Repeated START)	t ₂	After this period, the first clock pulse is generated.	0.6			μs
tLOW Low Period of SCL Clock	t ₃		1.3			μs
t _{HIGH} High Period of SCL Clock	t4		0.6		50	μs
t _{SU;STA} Setup Time for Repeated START Condition	t ₅		0.6			μs
t _{HD;DAT} Data Hold Time	t ₆				0.9	μs
tsu;dat Data Setup Time	t7		100			ns
t _F Fall Time of Both SDA and SCL Signals	t ₈				300	ns
$t_{\ensuremath{R}}$ Rise Time of Both SDA and SCL Signals	t9				300	ns
t _{SU;STO} Setup Time for STOP Condition	t ₁₀		0.6			μs

NOTES

- ⁵ Guaranteed by design and not subject to production test.
- ⁶ P_{DISS} is calculated from ($I_{DD} \times V_{DD}$). CMOS logic level inputs result in minimum power dissipation.
- 7 All dynamic characteristics use V_{DD} = 5 V.
- ⁸ See timing diagrams for locations of measured values.

¹ Typical specifications represent average readings at +25°C and $V_{DD} = 5$ V.

² Resistor position nonlinearity error R-INL is the deviation from an ideal value measured between the maximum resistance and the minimum resistance wiper positions. R-DNL measures the relative step change from ideal between successive tap positions. Parts are guaranteed monotonic. ³ $V_A = V_{DD}$, Wiper (V_W) = no connect.

⁴ Resistor terminals A and W have no limitations on polarity with respect to each other.

ABSOLUTE MAXIMUM RATINGS¹

 $(T_A = +25^{\circ}C, unless otherwise noted.)$

Table 4.

Parameter	Value
V _{DD} to GND	–0.3 V to +7 V
V _A , V _W to GND	V _{DD}
Terminal Current, Ax-Bx, Ax-Wx, Bx-Wx	
Pulsed ¹	±20 mA
Continuous	±5 mA
Digital Inputs and Output Voltage to GND	0 V to +7 V
Operating Temperature Range	–40°C to +125°C
Maximum Junction Temperature (T _{JMAX})	150°C
Storage Temperature	–65°C to +150°C
Lead Temperature (Soldering, 10 sec)	300°C
Thermal Resistance ² θ _{JA} : SC70-6	230°C/W

NOTES

¹ Maximum terminal current is bounded by the maximum current handling of the switches, maximum power dissipation of the package, and maximum applied voltage across any two of the A, B, and W terminals at a given resistance.

²Package power dissipation = $(T_{JMAX} - T_A)/\theta_{JA}$.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

I²C INTERFACE

Table 5. Write Mode

S	0	1	0	1	1	1	0	W	А	Х	D6	D5	D4	D3	D2	D1	D0	Α	Р
			Slave	e Adc	lress	Byte							Data	Byte					

Table 6. Read Mode

S	0	1	0	1	1	1	0	R	А	0	D6	D5	D4	D3	D2	D1	D0	А	Р
			Slav	ve Ado	dress E	Byte							Data	Byte					

- S = Start Condition
- P = Stop Condition
- A = Acknowledge
- X = Don't Care

 $\overline{W} = Write$

R = Read

RS = Reset wiper to Midscale 40_H

SD = Shutdown connects wiper to B terminal and open circuits A terminal. It does not change contents of wiper register.

D6, D5, D4, D3, D2, D1, D0 = Data Bits



Figure 3. I²C Interface Detailed Timing Diagram



Figure 4. Writing to the RDAC Register



Figure 5. Reading Data from a Previously Selected RDAC Register in Write Mode

OPERATION

The AD5246 is a 128-position digitally controlled variable resistor (VR) device.

An internal power-on preset places the wiper at midscale during power-on, which simplifies the fault condition recovery at power-up.

PROGRAMMING THE VARIABLE RESISTOR *Rheostat Operation*

The nominal resistance of the RDAC between terminals A and B is available in 5 k Ω , 10 k Ω , 50 k Ω , and 100 k Ω . The final two or three digits of the part number determine the nominal resistance value, e.g., $10 \text{ k}\Omega = 10$; $50 \text{ k}\Omega = 50$. The nominal resistance (R_{AB}) of the VR has 128 contact points accessed by the wiper terminal, plus the B terminal contact. The 7-bit data in the RDAC latch is decoded to select one of the 128 possible settings. Assume a 10 k Ω part is used, the wiper's first connection starts at the B terminal for data 0x00. Since there is a 50 Ω wiper contact resistance, such connection yields a minimum of $2 \times 50 \Omega$ resistance between terminals W and B. The second connection is the first tap point, which corresponds to 178 Ω (R_{WB} = R_{AB}/128+ R_W = 78 Ω + 2 × 50 Ω) for data 0x01. The third connection is the next tap point, representing 256 Ω $(2 \times 78 \ \Omega + 2 \times 50 \ \Omega)$ for data 0x02, and so on. Each LSB data value increase moves the wiper up the resistor ladder until the last tap point is reached at 10,100 Ω (R_{AB} + 2 × R_W). Figure 6 shows a simplified diagram of the equivalent RDAC circuit.



Figure 6. AD5246 Equivalent RDAC Circuit

The general equation determining the digitally programmed output resistance between W and B is

$$R_{WB}(D) = \frac{D}{128} \times R_{AB} + 2 \times R_{W} \tag{1}$$

where *D* is the decimal equivalent of the binary code loaded in the 7-bit RDAC register, R_{AB} is the end-to-end resistance, and R_W is the wiper resistance contributed by the on resistance of the internal switch.

In summary, if $R_{AB} = 10 \text{ k}\Omega$ and the A terminal is open circuited, the following output resistance R_{WB} will be set for the indicated RDAC latch codes.

D (Dec.)	R _{WB} (Ω)	Output State
127	10,100	Full Scale ($R_{AB} + 2 \times R_W$)
64	5,100	Midscale
1	178	1 LSB
0	100	Zero Scale (Wiper Contact Resistance)

Note that in the zero-scale condition a finite wiper resistance of 100 Ω is present. Care should be taken to limit the current flow between W and B in this state to a maximum pulse current of no more than 20 mA. Otherwise, degradation or possible destruction of the internal switch contact can occur.

Typical device to device matching is process lot dependent and may vary by up to $\pm 30\%$. Since the resistance element is processed in thin film technology, the change in R_{AB} with temperature has a very low 35 ppm/°C temperature coefficient.

I²C COMPATIBLE 2-WIRE SERIAL BUS

The first byte of the AD5246 is a slave address byte (see Table 5 and Table 6). It has a 7-bit slave address and a R/\overline{W} bit. The seven MSBs of the slave address are 0101110 followed by 0 for a write command or 0 to place the device in read mode.

The 2-wire I²C serial bus protocol operates as follows:

1. The master initiates data transfer by establishing a START condition, which is when a high-to-low transition on the SDA line occurs while SCL is high (see Figure 4). The following byte is the slave address byte, which consists of the 7-bit slave address followed by an R/\overline{W} bit (this bit determines whether data will be read from or written to the slave device).

The slave whose address corresponds to the transmitted address responds by pulling the SDA line low during the ninth clock pulse (this is termed the acknowledge bit). At this stage, all other devices on the bus remain idle while the

selected device waits for data to be written to or read from its serial register. If the R/\overline{W} bit is high, the master will read from the slave device. On the other hand, if the R/\overline{W} bit is low, the master will write to the slave device.

- 2. In the write mode, after acknowledgement of the slave address byte, the next byte is the data byte. Data is transmitted over the serial bus in sequences of nine clock pulses (eight data bits followed by an acknowledge bit). The transitions on the SDA line must occur during the low period of SCL and remain stable during the high period of SCL (see Table 5).
- 3. In the read mode, after acknowledgment of the slave address byte, data is received over the serial bus in sequences of nine clock pulses (a slight difference with the write mode, where there are eight data bits followed by an acknowledge bit). Similarly, the transitions on the SDA line must occur during the low period of SCL and remain stable during the high period of SCL (see Figure 5).
- 4. When all data bits have been read or written, a STOP condition is established by the master. A STOP condition is defined as a low-to-high transition on the SDA line while SCL is high. In write mode, the master will pull the SDA line high during the tenth clock pulse to establish a STOP condition (see Figure 4). In read mode, the master will issue a No Acknowledge for the ninth clock pulse (i.e., the SDA line remains high). The master will then bring the SDA line low before the tenth clock pulse which goes high to establish a STOP condition (see Figure 5).

A repeated write function gives the user flexibility to update the RDAC output a number of times after addressing the part only once. For example, after the RDAC has acknowledged its slave address in the write mode, the RDAC output will update on each successive byte. If different instructions are needed, the write/read mode has to start again with a new slave address and data byte. Similarly, a repeated read function of the RDAC is also allowed.

LEVEL SHIFTING FOR BIDIRECTIONAL INTERFACE

While most legacy systems may be operated at one voltage, a new component may be optimized at another. When two systems operate the same signal at two different voltages, proper level shifting is needed. For instance, one can use a 3.3 V E^2PROM to interface with a 5 V digital potentiometer. A level shifting scheme is needed to enable a bidirectional communication so that the setting of the digital potentiometer can be stored to and retrieved from the E^2PROM . Figure 7 shows one of the implementations. M1 and M2 can be any N-channel signal FETs, or if V_{DD} falls below 2.5 V, low threshold FETs such as the FDV301N.



Figure 7. Level Shifting for Operation at Different Potentials

ESD PROTECTION

All digital inputs are protected with a series input resistor and parallel Zener ESD structures shown in Figure 8 and Figure 9. This applies to the digital input pins SDA and SCL.



Figure 8. ESD Protection of Digital Pins



Figure 9. ESD Protection of Resistor Terminals

TERMINAL VOLTAGE OPERATING RANGE

The AD5246 V_{DD} and GND power supply defines the boundary conditions for proper 3-terminal digital potentiometer operation. Supply signals present on terminals B and W that exceed V_{DD} or GND will be clamped by the internal forward biased diodes (see Figure 10).



Figure 10. Maximum Terminal Voltages Set by VDD and Vss

POWER-UP SEQUENCE

Since the ESD protection diodes limit the voltage compliance at terminals B and W (see Figure 10), it is important to power V_{DD}/GND before applying any voltage to terminals B and W; otherwise, the diode will be forward biased such that V_{DD} will be powered unintentionally and may affect the rest of the user's circuit. The ideal power-up sequence is in the following order: GND, V_{DD} , digital inputs, and then $V_{B/W}$. The relative order of powering V_B and V_W , and the digital inputs is not important as long as they are powered after V_{DD}/GND .

LAYOUT AND POWER SUPPLY BYPASSING

It is a good practice to employ compact, minimum lead length layout design. The leads to the inputs should be as direct as possible with a minimum conductor length. Ground paths should have low resistance and low inductance.

Similarly, it is also a good practice to bypass the power supplies with quality capacitors for optimum stability. Supply leads to the

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device should be bypassed with disc or chip ceramic capacitors of 0.01 μ F to 0.1 μ F. Low ESR 1 μ F to 10 μ F tantalum or electrolytic capacitors should also be applied at the supplies to minimize any transient disturbance and low frequency ripple (see Figure 11). Note that the digital ground should also be joined remotely to the analog ground at one point to minimize the ground bounce.



Figure 11. Power Supply Bypassing

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

PIN CONFIGURATION



PIN FUNCTION DESCRIPTIONS

Table 8.

1 401	• • • •	
Pin	Name	Description
1	V _{DD}	Positive Power Supply.
2	GND	Digital Ground.
3	SCL	Serial Clock Input. Positive edge triggered.
4	SDA	Serial Data Input/Output.
5	W	W Terminal.
6	В	B Terminal.

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OUTLINE DIMENSIONS

6-Lead SC70 (KS)



Figure 13. 6-Lead Thin Shrink Small Outline Transistor [SC70] (KS-6) Dimensions shown in millimeters

ORDERING GUIDE

Model	R _{AB} (Ω)	Temperature	Package Description	Package Option	Branding
AD5246BKS5-R2	5k	-40°C to +125°C	6-lead SC70	KS-6	D16
AD5246BKS5-RL7	5k	-40°C to +125°C	6-lead SC70	KS-6	D16
AD5246BKS10-R2	10k	-40°C to +125°C	6-lead SC70	KS-6	D1D
AD5246BKS10-RL7	10k	-40°C to +125°C	6-lead SC70	KS-6	D1D
AD5246BKS50-R2	50k	-40°C to +125°C	6-lead SC70	KS-6	D1C
AD5246BKS50-RL7	50k	-40°C to +125°C	6-lead SC70	KS-6	D1C
AD5246BKS100-R2	100k	-40°C to +125°C	6-lead SC70	KS-6	D1A
AD5246BKS100-RL7	100k	-40°C to +125°C	6-lead SC70	KS-6	D1A
AD5246EVAL	See Note 1		Evaluation Board		

¹The evaluation board is shipped with the 10 k Ω R_{AB} resistor option; however, the board is compatible with all available resistor value options.

The AD5246 contains 1976 transistors. Die size: $32 \text{ mil} \times 39 \text{ mil} = 1,248 \text{ sq. mil}$.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



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